

# QUAD CMOS-TO-MOS DRIVER

## For 4K N-Channel MOS RAMs

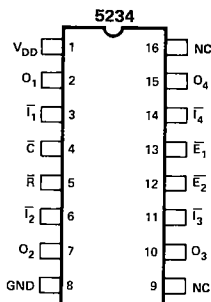
- CMOS Technology for Very Low Power: Suitable for Battery Backup
- High Density: Four Drivers in One Package
- Internal Gating Structure Minimizes Package Count
- CMOS Compatible Inputs
- CerDIP Package: 16 Pin DIP
- Only One Power Supply Required, +12V ( $\pm 10\%$ )

MEMORY  
SUPPORT

The Intel® 5234 is a Quad CMOS-to-MOS driver which accepts CMOS input signals. It provides high output current and voltage suitable for driving the clock inputs of N-channel MOS memories such as the 2107A or 2107B. The circuit operates from a single 12 volt power supply.

The device features two common enable inputs, a refresh select input, and a clock control input for simplified system design. The Intel ion-implanted, silicon gate, Complementary MOS (CMOS) process allows the design and production of very low power drivers.

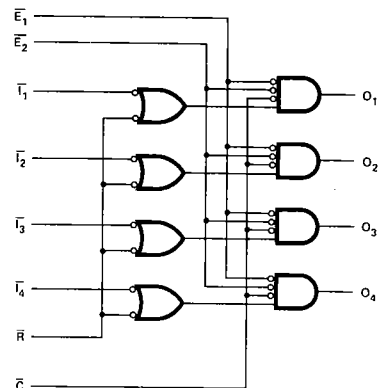
### PIN CONFIGURATION



### PIN NAMES

$I_1, I_4$	SELECT INPUTS	$\bar{C}$	CLOCK CONTROL INPUT
$\bar{E}_1, \bar{E}_2$	ENABLE INPUTS	$O_1, O_4$	DRIVER OUTPUTS
$\bar{R}$	REFRESH SELECT INPUT	$V_{DD}$	+12V POWER SUPPLY
		NC	NOT CONNECTED

### LOGIC DIAGRAM



## Absolute Maximum Ratings\*

Temperature Under Bias	-10°C to 80°C
Storage Temperature	-65°C to +150°C
Supply Voltage, $V_{DD}$	-0.5 to +14V
All Input Voltages	-0.5 to ( $V_{DD}+0.5V$ )
Outputs for Clock Driver	-0.5 to ( $V_{DD}+0.5V$ )
Power Dissipation at 25°C	1W

\*COMMENT: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## D.C. Characteristics

$T_A = 0^\circ\text{C}$  to  $70^\circ\text{C}$ ,  $V_{DD} = 12V \pm 10\%$ .

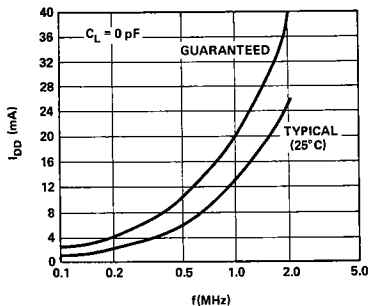
Symbol	Parameter	Min.	Typ. <sup>[1]</sup>	Max.	Unit	Test Conditions
$ I_{LI} $	Input Load Current			0.1	$\mu\text{A}$	$V_{IN} = 0$ to $V_{DD}$
$V_{OL}$	Output Low Voltage		0.15	0.4	V	$I_{OL} = 5\text{mA}$
		-1.0	-0.15			$I_{OL} = -5\text{mA}$
$V_{OH}$	Output High Voltage	$V_{DD}-0.4$	$V_{DD}-0.15$		V	$I_{OH} = -5\text{mA}$
			$V_{DD}+0.15$	$V_{DD}+0.5$		$I_{OH} = 5\text{mA}$
$V_{IL}$	Input Low Voltage, All Inputs			2.0	V	
$V_{IH}$	Input High Voltage, All Inputs	$V_{DD}-2.0$			V	
$I_{DD}$	Supply Current		0.1	100	$\mu\text{A}$	$V_{DD} = 13.2V$ , $f = 0$
$I_{DD1}$	Supply Current		13	20	mA	$V_{DD} = 13.2V$ , $f = 1\text{MHz}$ , $C_L = 0$ , (See Figure 1)

Note 1: Typical values are at 25°C and nominal voltage.

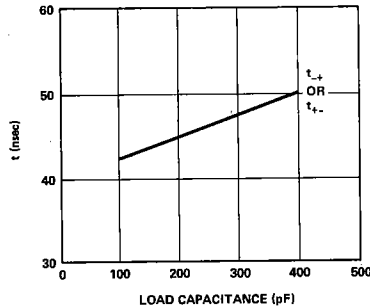
## Typical Characteristics

FIGURE 1

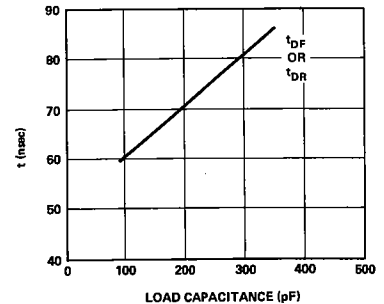
POWER SUPPLY CURRENT VS. FREQUENCY  
(ALL 4 CHANNELS SWITCHING)



INPUT TO OUTPUT DELAY  
VS. LOAD CAPACITANCE



DELAY PLUS TRANSITION TIME  
VS. LOAD CAPACITANCE



## A.C. Characteristics $T_A = 0^\circ \text{ to } 70^\circ \text{C}$ , $V_{DD} = 12\text{V} \pm 10\%$ .

Symbol	Parameter	Min.[1]	Typ.[2,4]	Max.[3]	Unit
$t_{L+}$	Input to Output Delay	20	45		ns
$t_{DR}$	Delay Plus Rise Time		70	100	ns
$t_{L-}$	Input to Output Delay	20	45		ns
$t_{DF}$	Delay Plus Fall Time		70	100	ns
$t_T$	Output Transition Time	10	25	40	ns

NOTES: 1.  $C_L = 150\text{pF}$   
 2.  $C_L = 200\text{pF}$   
 3.  $C_L = 250\text{pF}$   
 4. Typical values are measured at  $25^\circ \text{C}$ .

These values represent a range of total stray plus clock capacitance for nine 4K RAMs.

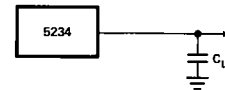
## Capacitance\* $T_A = 25^\circ \text{C}$

Symbol	Test	Typ.	Max.	Unit
$C_{IN}$	Input Capacitance	8	14	pF

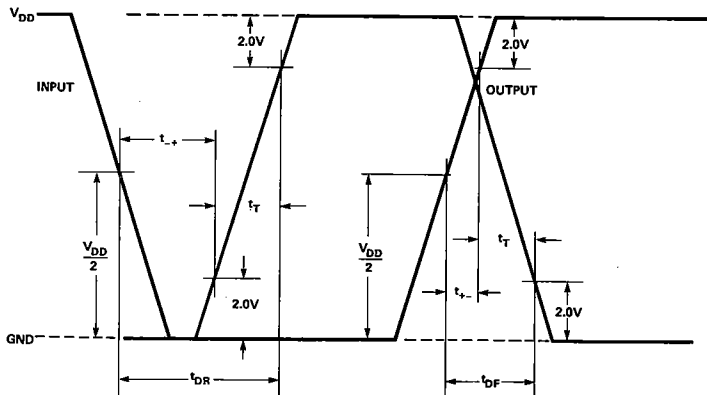
\*This parameter is periodically sampled and is not 100% tested.  
 Condition of measurement is  $f = 1\text{ MHz}$ ,  $V_{bias} = 2\text{V}$ ,  $V_{CC} = 0\text{V}$ , and  $T_A = 25^\circ \text{C}$ .

## A.C. CONDITIONS OF TEST

Input Pulse Amplitudes: 0 to  $V_{DD}$   
 Input Pulse Rise and Fall Times: 40 ns between 10% and 90% points  
 Measurement Points: See Waveforms



## Waveforms



## Typical System

Below is an example of a 64K x 18 bit memory system (each card is 16K x 18) employing the 5234 quad high voltage driver for the chip enable inputs. A single 5234 package drives 16K x 9 bits. A<sub>0</sub> through A<sub>11</sub> are 2107B addresses.

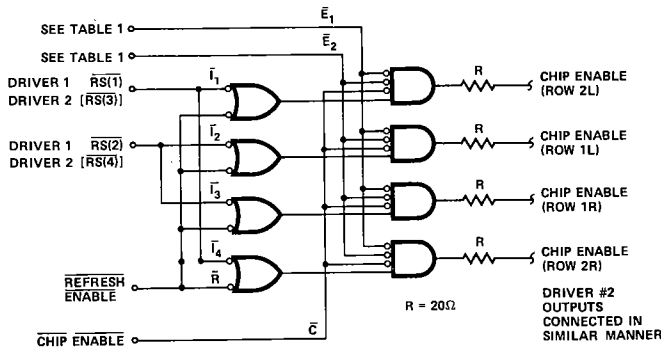
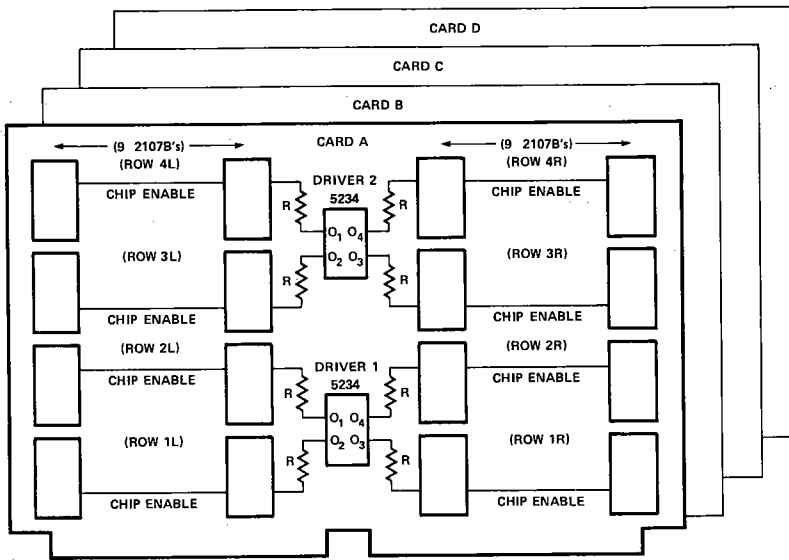


TABLE 1.

CARD	INPUTS
A	ENABLE M
B	ENABLE M
C	ENABLE N
D	ENABLE N

